

N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω) MAX.	I _D (A)	Q _g (TYP.)			
80	1.2 at V _{GS} = 10 V	300	253 nC			

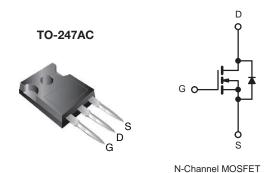
FEATURES

- DT-TrenchPower MOSFET
- \bullet 100 % R_g and UIS tested
- Improved dv/dt capability



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- Hard Switched and High Frequency Circuits



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER		LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	80	V				
Gate-Source Voltage	V_{GS}	± 20	V				
Continuous Drain Current (T,I = 150 °C)	T _C = 25 °C		300				
Continuous Drain Current (1) = 150 C)	T _C = 100 °C	l _D	175				
Pulsed Drain Current (t = 100 μs)	I _{DM}	1250	А				
Avalanche Current	L = 0.1 mH	I _{AS}	100				
Single Avalanche Energy ^a	L=0.1 IIII	E _{AS}	3395	mJ			
Maximum Dawar Discipation 2	T _C = 25 °C	D.	442 ^b	W			
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	88.4 ^b				
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +150	°C				

THERMAL RESISTANCE RATINGS					
PARAMETER		LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	60	°C/W		
Junction-to-Case (Drain)	R_{thJC}	0.4			

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2	-	2.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA	
Zero date voltage Drain Julient	I _{DSS}	V_{DS} = 64 V, V_{GS} = 0 V, T_J = 85 °C	-	-	10		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	1.2	1.6	mΩ	
Forward Transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 3 A	-	22	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	15630	-		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 40 \text{ V}, f = 1 \text{ MHz}$	-	3295	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	290	-		
Total Gate Charge ^c	Q_g		-	253	-		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	39	-	nC	
Gate-Drain Charge ^c	Q_{gd}		-	82	-		
Gate Resistance	R_g	f = 1 MHz	-	1.0	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	53	-		
Rise Time ^c	t _r	V_{DD} = 40 V, R_L = 1.67 Ω	-	220	-		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 30$ A, V_{GEN} = 10 V, R_g = 1 Ω	-	167	-	ns	
Fall Time ^c	t _f		-	180	-	1	
Drain-Source Body Diode Ratings ar	d Characteri	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1250	Α	
Forward Voltage ^a	V_{SD}	I _F = 30 A, V _{GS} = 0 V	-	-	1.0	V	
Reverse Recovery Time	t _{rr}		-	120	-	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	7	-	Α	
Reverse Recovery Charge	Q_{rr}		-	350	-	nC	

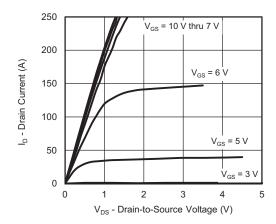
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

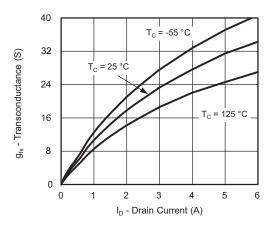
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



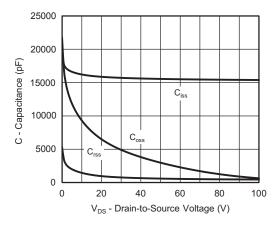
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



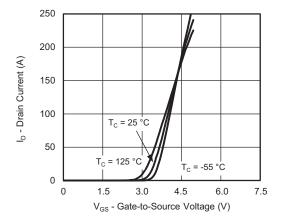
Output Characteristics



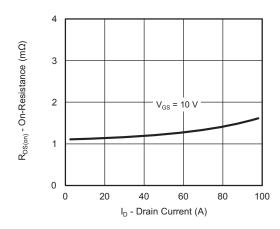
Transconductance



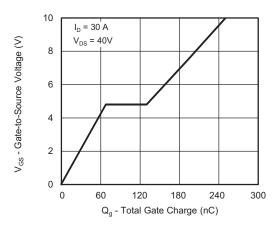
Capacitance



Transfer Characteristics



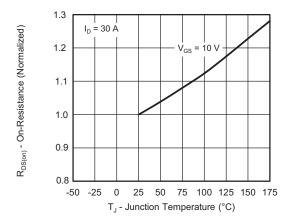
On-Resistance vs. Drain Current



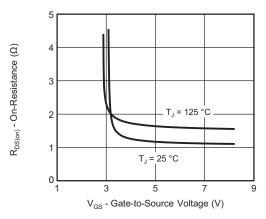
Gate Charge



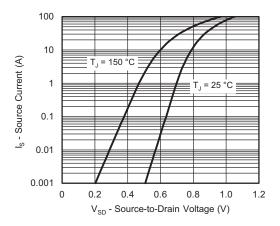
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



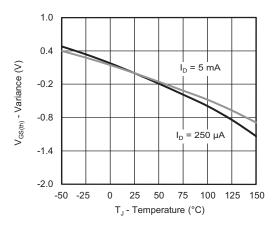
On-Resistance vs. Junction Temperature



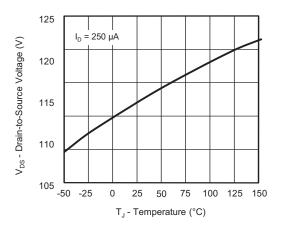
On-Resistance vs. Gate-to-Source Voltage



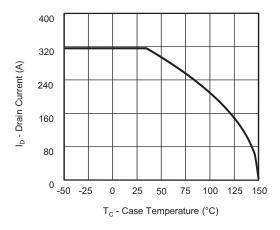
Source Drain Diode Forward Voltage



Threshold Voltage



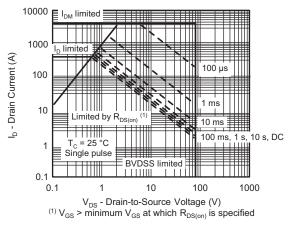
Drain Source Breakdown vs. Junction Temperature



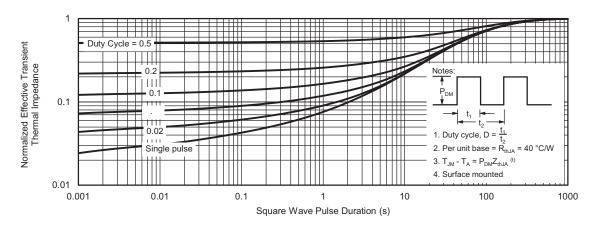
Current De-Rating



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



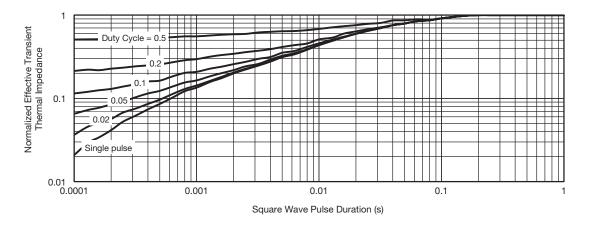
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

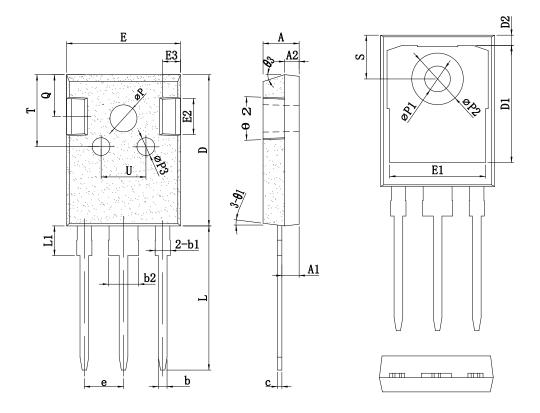
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



TO-247_3L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.60	5.00	5.40	e	2.10	5.44	5.70
A1	2.10	2.41	2.70	L	19.00	19.98	21.00
A2	1.70	2.00	2.30	L1	,	-	4.50
b	1.00	1.20	1.40	ФР	3.30	3.70	4.00
bl	1.80	2.10	2.40	ФР1	3.25	3.55	3.85
b2	2.80	3.10	3.40	ФР2	6.80	7.18	7.60
С	0.45	0.60	0.75	ФР3	2.30	2.50	3.30
D	19.00	21.00	23.00	Q	5.50	5.80	6.30
D1	16.00	16.55	17.00	S	5.60	6.15	6.30
D2	0.95	1.20	1.45	T	9.50	10.00	10.50
Е	15.70	15.80	16.50	U	6.00	-	8.00
E1	12.80	13.25	13.70	θ1	5°	7°	9°
E2	4.20	5.00	5.30	θ2	1°	3°	5°
E3	2.20	2.50	2.80	θ3	13°	15°	17°





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